

**General Description**

- Trench Power MOSFET technology
- Low  $R_{DS(ON)}$  and Gate Charge
- Enhanced Robustness
- RoHS and Halogen-Free Compliant

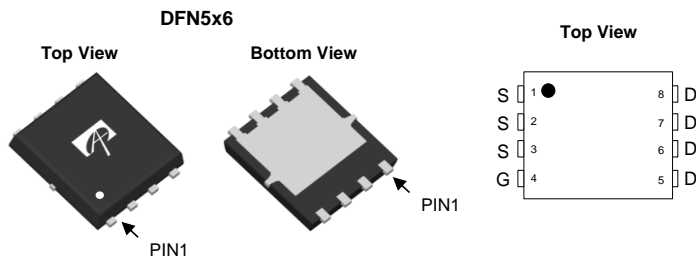
**Applications**

- High Frequency Switching and Synchronous Rectification

**Product Summary**

$V_{DS}$	150V
$I_D$ (at $V_{GS}=10V$ )	100A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 9.8m $\Omega$
$R_{DS(ON)}$ (at $V_{GS}=8V$ )	< 11.5m $\Omega$

100% UIS Tested  
 100% Rg Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AONS66521	DFN 5X6	Tape & Reel	3000

**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	150	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	100	A
Current		$T_C=25^\circ\text{C}$	
		64	
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	400	
Continuous Drain Current	$I_{DSM}$	16	A
Current		$T_A=25^\circ\text{C}$	
		13	
Avalanche Current <sup>C</sup>	$I_{AS}$	40	A
Avalanche energy $L=0.3\text{mH}$ <sup>C</sup>	$E_{AS}$	240	mJ
Diode reverse recovery	$dv/dt$	30	V/ns
$V_{DS}=0$ to $75\text{V}$ , $I_F \leq 10\text{A}$ , $T_j=25^\circ\text{C}$	$di/dt$	500	A/us
Power Dissipation <sup>B</sup>	$P_D$	215	W
		$T_C=25^\circ\text{C}$	
		86	
Power Dissipation <sup>A</sup>	$P_{DSM}$	6.2	W
		$T_A=25^\circ\text{C}$	
		4	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	15	20	$^\circ\text{C/W}$
		$t \leq 10\text{s}$		
Maximum Junction-to-Ambient <sup>A,D</sup>		40	50	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	0.43	0.58	$^\circ\text{C/W}$

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	150			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =150V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	3.5	4	4.5	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =20A T <sub>J</sub> =125°C		8.2	9.8	mΩ
		V <sub>GS</sub> =8V, I <sub>D</sub> =20A		15	18	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A		50		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.7	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				100	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =75V, f=1MHz		2600		pF
C <sub>oss</sub>	Output Capacitance			340		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			3.2		pF
R <sub>g</sub>	Gate resistance	f=1MHz	0.7	1.45	2.2	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g(10V)</sub>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =75V, I <sub>D</sub> =20A		32	45	nC
Q <sub>gs</sub>	Gate Source Charge			14		nC
Q <sub>gd</sub>	Gate Drain Charge			6.2		nC
Q <sub>oss</sub>	Output Charge	V <sub>GS</sub> =0V, V <sub>DS</sub> =75V		120		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =75V, R <sub>L</sub> =3.75Ω, R <sub>GEN</sub> =3Ω		16		ns
t <sub>r</sub>	Turn-On Rise Time			4.5		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			22.5		ns
t <sub>f</sub>	Turn-Off Fall Time			11		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =20A, di/dt=500A/μs		68		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =20A, di/dt=500A/μs		640		nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The Power dissipation P<sub>DSM</sub> is based on R<sub>θJA</sub> ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

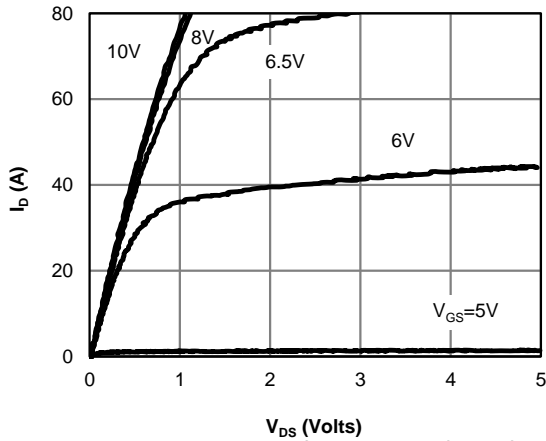
H. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C.

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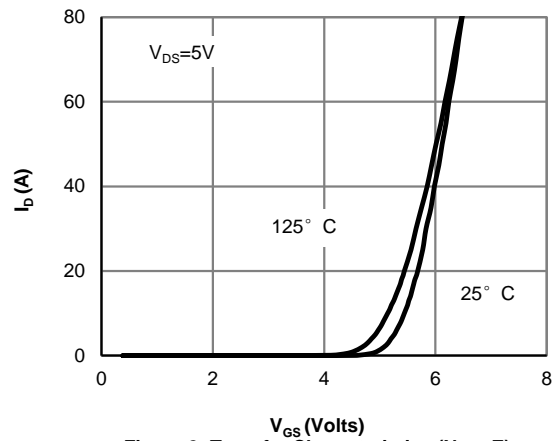
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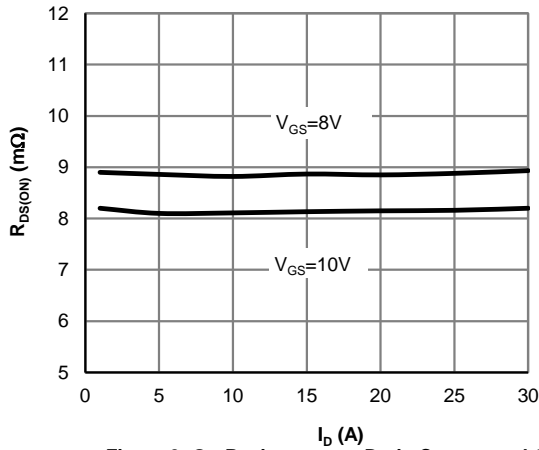
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



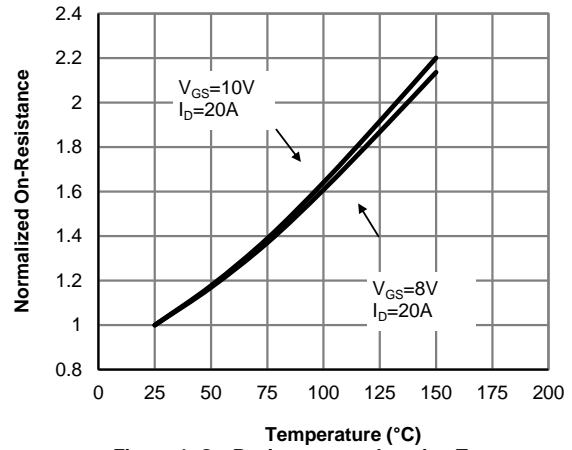
**Figure 1: On-Region Characteristics (Note E)**



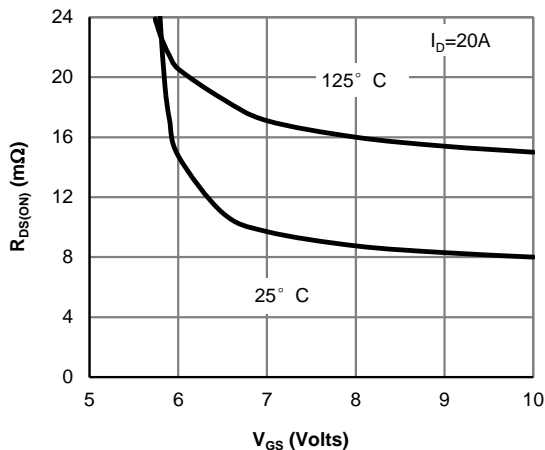
**Figure 2: Transfer Characteristics (Note E)**



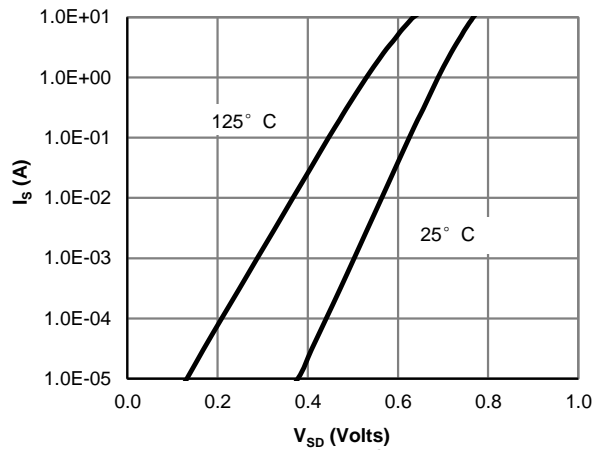
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

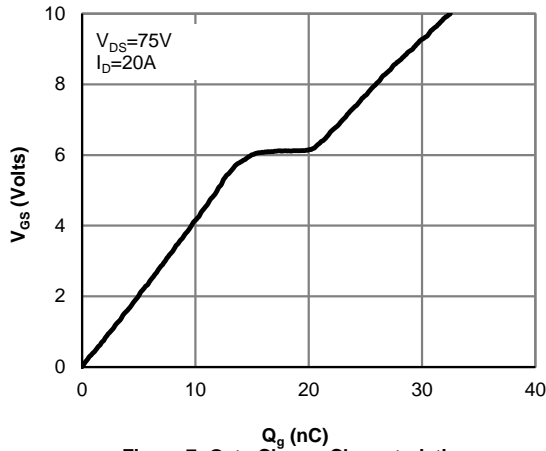


**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

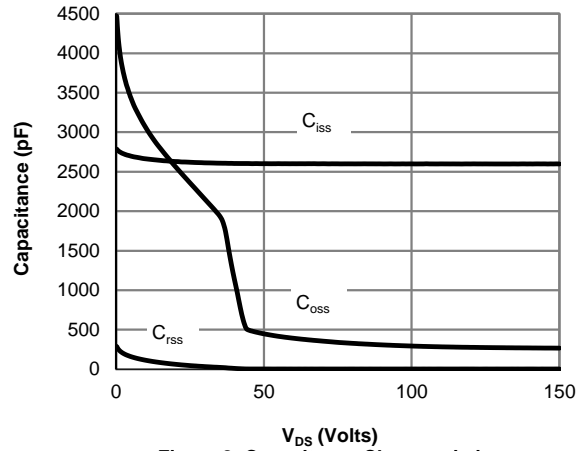


**Figure 6: Body-Diode Characteristics (Note E)**

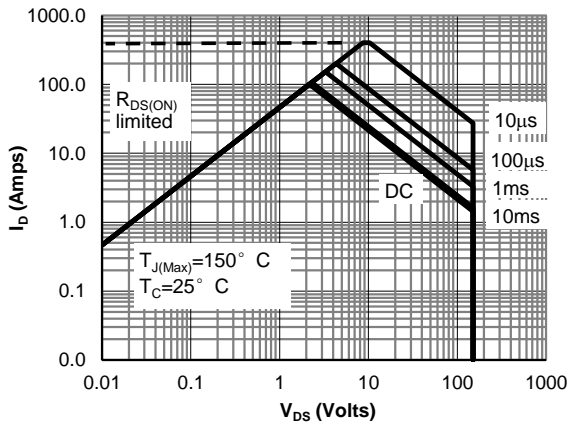
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



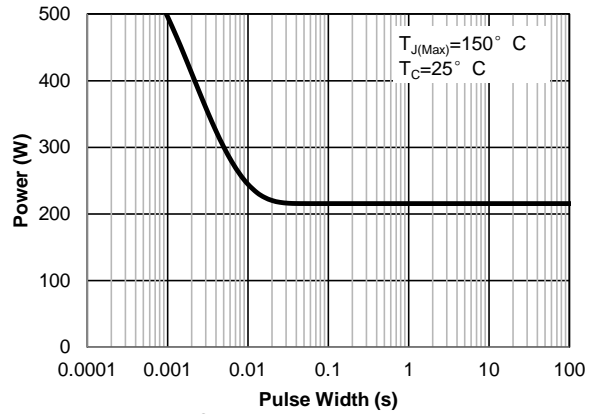
**Figure 7: Gate-Charge Characteristics**



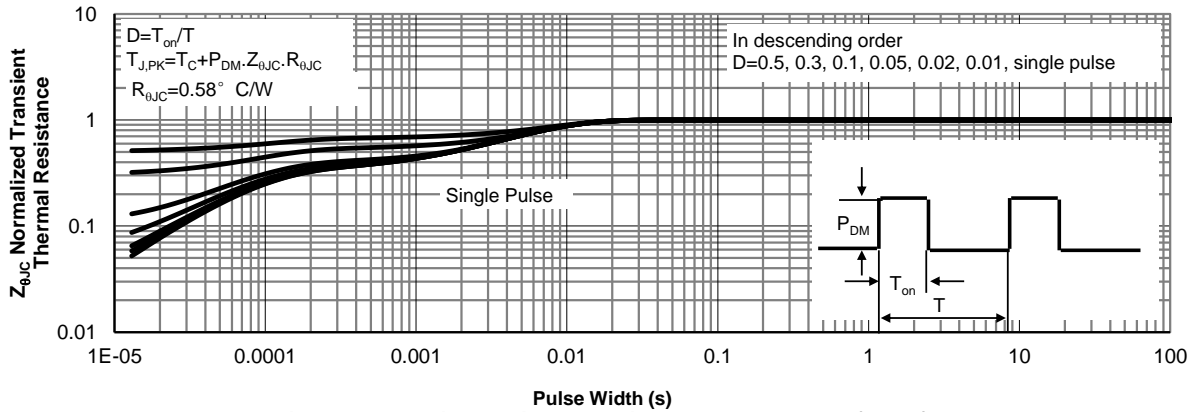
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area (Note F)**



**Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)**



**Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)**

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

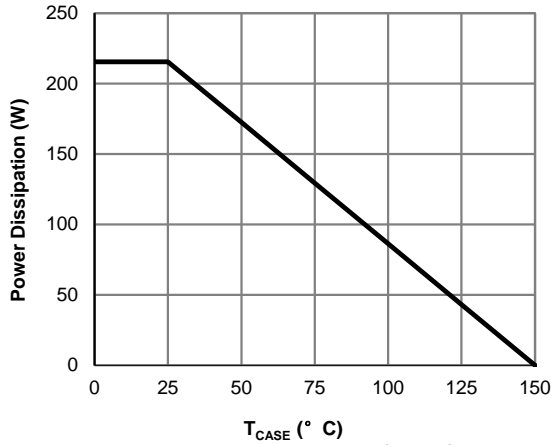


Figure 12: Power De-rating (Note F)

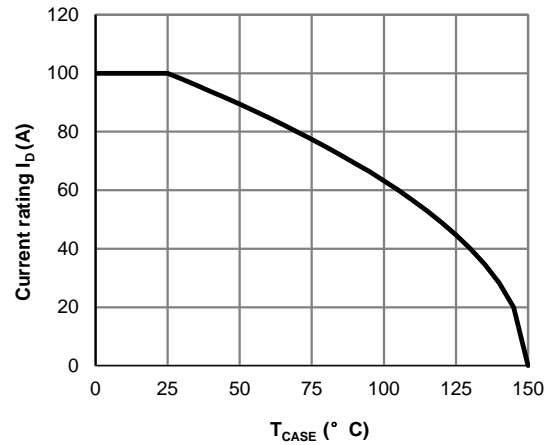


Figure 13: Current De-rating (Note F)

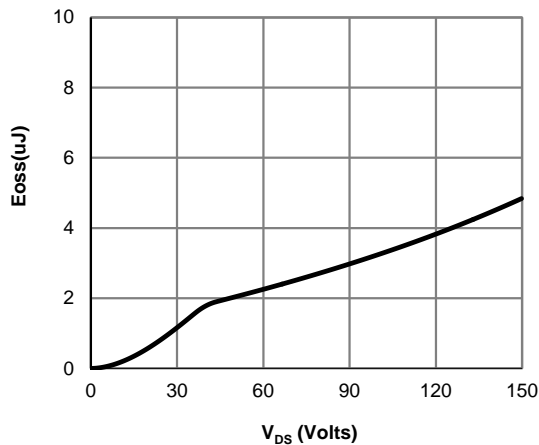


Figure 14: Coss stored Energy

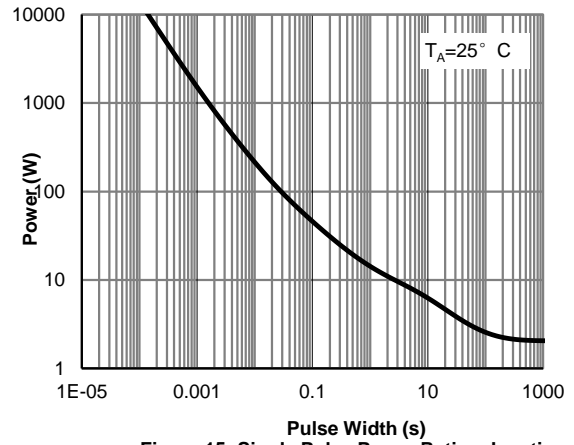


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

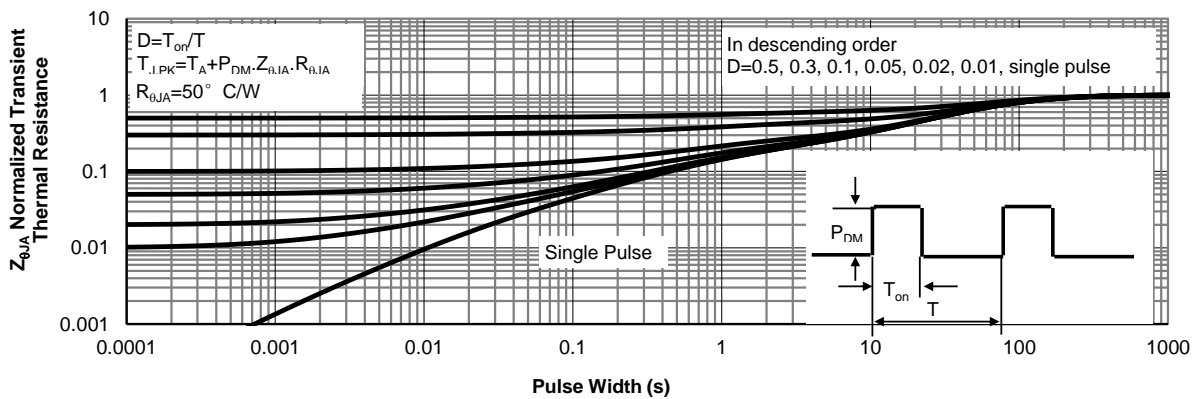


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

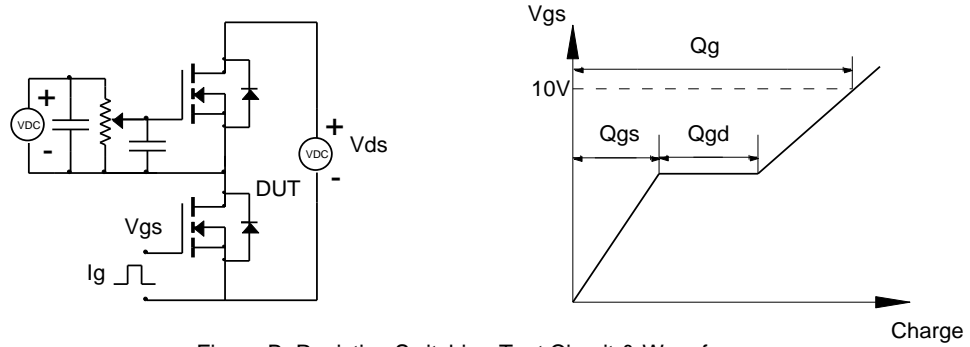


Figure B: Resistive Switching Test Circuit & Waveforms

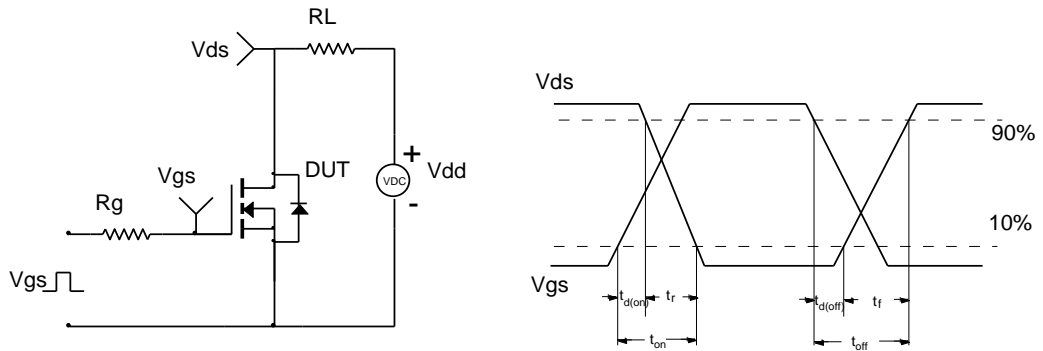


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

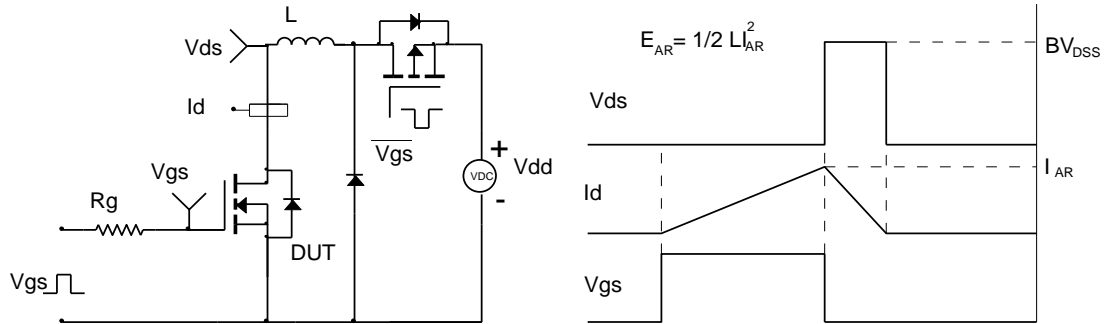


Figure D: Diode Recovery Test Circuit & Waveforms

